

MRF237

CASE 79-03, STYLE 5 HIGH FREQUENCY TRANSISTOR

NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CE0}	18	Vdc
Collector-Base Voltage	V_{CBO}	36	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	640	mAdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	8.0 45.7	Watts mW/ $^\circ\text{C}$
Storage Temperature	T_{stg}	- 65 to + 200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	20	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 10 \text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	18	—	—	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 5.0 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	36	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 1.0 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 15 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	0.25	mAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 250 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	5.0	—	—	—
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance ($V_{CB} = 15 \text{ Vdc}$, $I_E = 0$, $f = 0.1 \text{ MHz}$)	C_{obo}	—	15	20	pF
FUNCTIONAL TEST (FIGURE 1)					
Common-Emitter Amplifier Power Gain ($P_{out} = 4.0 \text{ W}$, $V_{CC} = 12.5 \text{ Vdc}$, $I_{C(max)} = 640 \text{ mAdc}$, $f = 175 \text{ MHz}$)	G_{PE}	12	14	—	dB
Collector Efficiency ($P_{out} = 4.0 \text{ W}$, $V_{CC} = 12.5 \text{ Vdc}$, $I_{C(max)} = 640 \text{ mAdc}$, $f = 175 \text{ MHz}$)	η	50	62	—	%

FIGURE 1 – 175 MHz TEST CIRCUIT SCHEMATIC

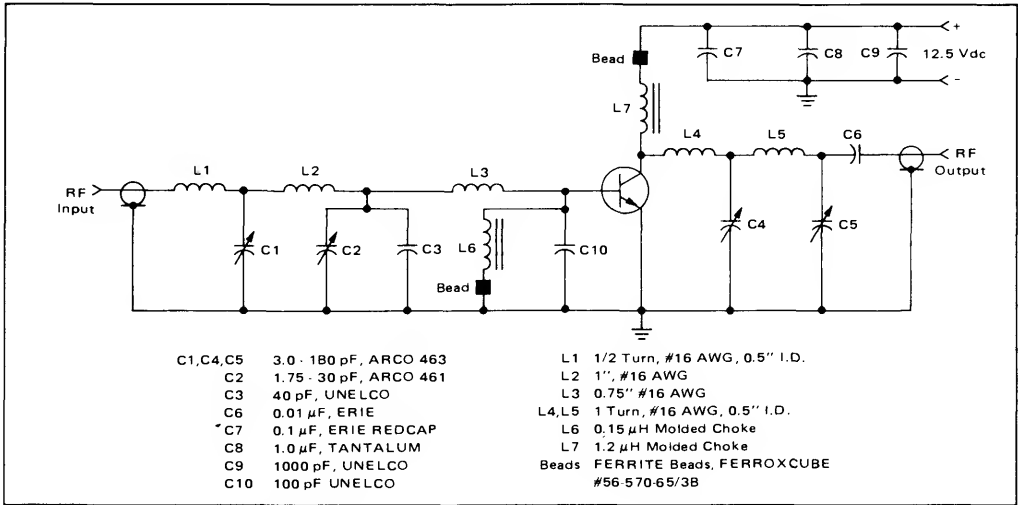


FIGURE 2 – OUTPUT POWER versus INPUT POWER

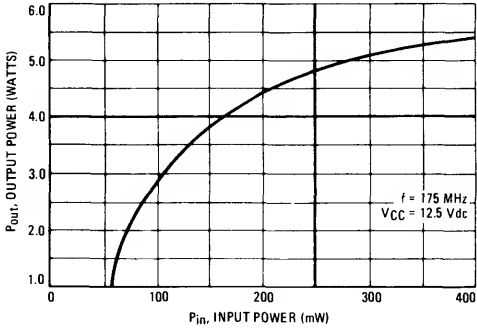


FIGURE 3 – OUTPUT POWER versus FREQUENCY

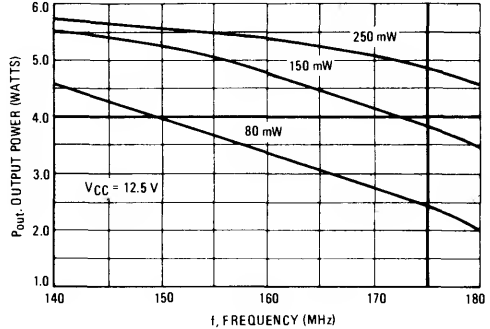


FIGURE 4 – OUTPUT POWER versus SUPPLY VOLTAGE

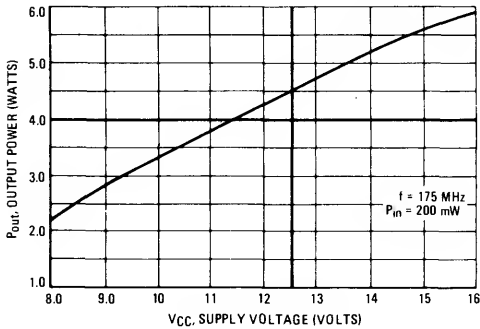


FIGURE 5 – SERIES EQUIVALENT IMPEDANCE

